

2N6082

SILICON BIPOLAR NPN POWER TRANSISTOR 25 W, in the 130 – 230 MHz Range

The silicon bipolar n-p-n transistor is designed primarily for VHF mobile and marine transmitters .

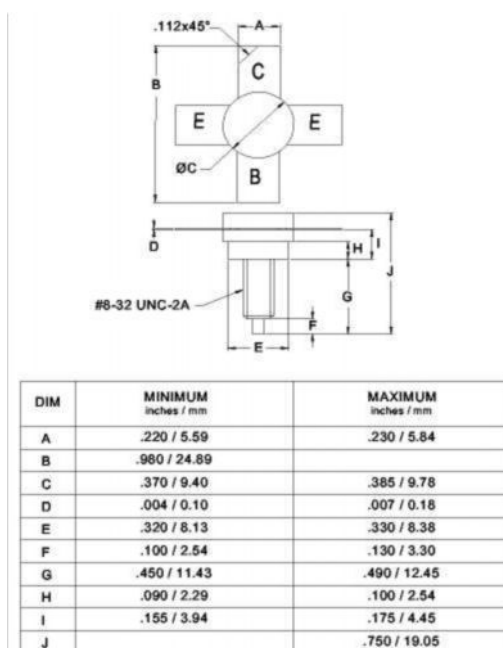
Features (At 175 MHz):

- Output Power: 25 W
- Power Gain: 6.2 dB Min
- Efficiency: 50% Min
- Common Emitter

Absolute Maximum Ratings

Parameters	Sym	Value	Unit
Collector–Emitter Voltage	V_{CEO}	18	V_{DC}
Collector-Base Voltage	V_{CBO}	36	V_{DC}
Emitter–Base Voltage	V_{EBO}	4	V_{DC}
Collector Current	$I_{C(max)}$	4	A_{DC}
Operation Junction Temperature	T_j	-65 ÷ +200	°C
Storage Temperature Range	T_{STG}	-65 ÷ +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.8	°C/W
Total Power Dissipation, $T_C=25^\circ C$	P_D	65	W

PACKAGE STYLE .380 4L STUD



Parameters

Parameter	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage ($I_C = 100 \text{ mA}$, $I_B = 0 \text{ A}$)	$V_{(BR)CEO}$	18	—	—	V_{DC}
Collector–Emitter Breakdown Voltage ($I_C = 20 \text{ mA}$, $V_{BE} = 0 \text{ V}$)	$V_{(BR)CER}$	36	—	—	V_{DC}
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ mA}$, $I_C = 0 \text{ A}$)	$V_{(BR)EBO}$	4	—	—	V_{DC}
Collector–Base Leakage Current ($V_{CB} = 15 \text{ V}$, $I_E = 0 \text{ A}$)	I_{CBO}	—	—	1.0	mA_{DC}
DC Current Gain ($V_{CE} = 5 \text{ V}$, $I_C = 0.25 \text{ A}$)	h_{FE}	5	—	100	
Output Capacitance ($V_{CB} = 15 \text{ V}$, $I_C = 0 \text{ A}$, $f = 1 \text{ MHz}$)	C_{OB}	—	—	130	pF
Power Gain ($V_{CB} = 12.5 \text{ V}$, $P_{OUT} = 25 \text{ W}$, $f = 175 \text{ MHz}$)	G_p	6.2	—	—	dB
Drain Efficiency ($V_{CB} = 12.5 \text{ V}$, $P_{OUT} = 25 \text{ W}$, $f = 175 \text{ MHz}$)	η_C	50	—	—	%

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Specification is subject to change without notice